

P-Ch MOSFET

General Description

The WST2035 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST2035 meet the RoHS and Green Product requirement , with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Product Summery

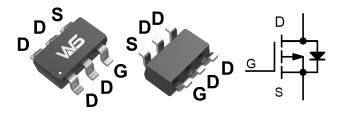
BVDSS	RDSON	ID
-20V	37mΩ	-4A

Applications

- Portable Equipment and Battery Powered Systems.
- Power Management in Notebook

Computer

SOT- 23-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±8	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ -4.5V ¹	-4	A
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ -4.5V ¹	-3.2	A
I _{DM}	Pulsed Drain Current ²	-30	A
P _D @T _A =25℃	Total Power Dissipation ³	0.35	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{eja}	Thermal Resistance Junction-Ambient ¹		357	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		85	°C/W



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Electrical Characteristics (T_J=25⁻¹C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-20			V	
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.016		V/℃	
D	Static Drain-Source On-Resistance ²	V_{GS} =-4.5V , I _D =-4.0A		37	50	mO	
R _{DS(ON)}		V_{GS} =-2.5V , I _D =-4.0A		45	60	mΩ	
V _{GS(th)}	Gate Threshold Voltage		-0.3	-0.56	-1.0	V	
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID2300A		3.97		mV/℃	
la se	Drain-Source Leakage Current	$V_{\text{DS}}\text{=-20V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathbb{C}$			-1	uA	
I _{DSS}		V_{DS} =-20V , V_{GS} =0V , T_J =125 $^\circ$ C			-30	uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = \pm 10V , V_{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-3A	8	16		S	
Qg	Total Gate Charge (-4.5V)			17.2			
Q _{gs}	Gate-Source Charge	$V_{\text{DS}}\text{=-}16\text{V}$, $V_{\text{GS}}\text{=-}4.5\text{V}$, $I_{\text{D}}\text{=-}4.0\text{A}$		1.3		nC	
Q_gd	Gate-Drain Charge			4.5			
T _{d(on)}	Turn-On Delay Time			9.5			
Tr	Rise Time	$V_{\text{DD}}\text{=-10V}$, $V_{\text{GEN}}\text{=-4.5V}$,		17		ns	
T _{d(off)}	Turn-Off Delay Time	$R_G=6\Omega$, $I_D=-4A$		94		115	
T _f	Fall Time			35			
C _{iss}	Input Capacitance			1450			
Coss	Output Capacitance	V _{DS} =-10V , V _{GS} =0V , f=1MHz		205		pF	
C _{rss}	Reverse Transfer Capacitance			160			

Diode Characteristics

Symbol	Parameter	neter Conditions		Тур.	Max.	Unit
ls	Continuous Source Current ^{1,4}				-1.0	А
I _{SM}	Pulsed Source Current ^{2,4}	$V_G=V_D=0V$, Force Current			-4.0	А
V _{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =-1A , T_{J} =25 $^{\circ}$ C			-1.2	V
t _{rr}	Reverse Recovery Time			9.5		nS
Q _{rr}	Reverse Recovery Charge	IF=-4.0A,dI/dt=100A/µs , Tյ=25℃		94		nC

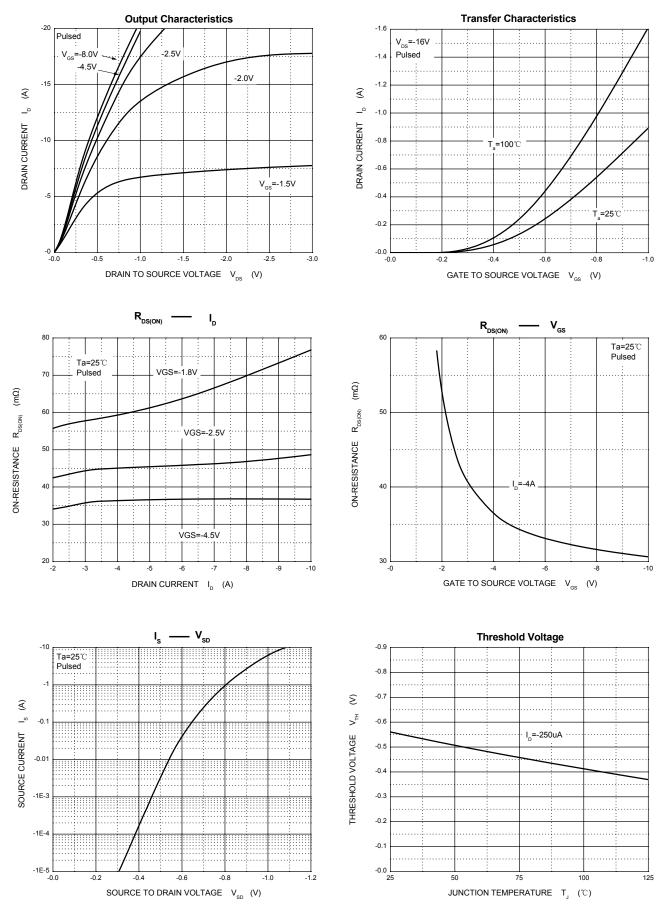
Notes:

- 1. Repetit e rating, pulse width limited by junction temperature.
- 2. Puls Test : Pulse width \leq 300µs, duty cycle \leq 2%.
- 3. These parameters have no way to verify.



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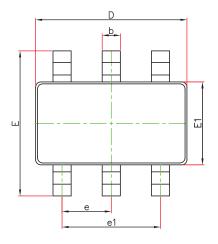
Typical Characteristics

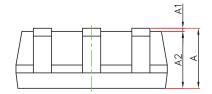


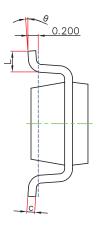


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SOT-23-6L Package Outline Dimensions

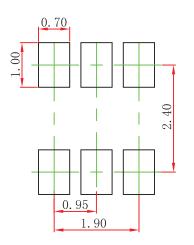






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E1	1.500	1.700	0.059	0.067	
E	2.650	2.950	0.104	0.116	
е	0.950((BSC) 0.037(BSC)		(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

SOT-23-6L Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.



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